SOLID STATE PHYSICISTS

Openings for Physicists and Metallurgists for basic research in Epitaxial growth and physical properties of semi-conductors; semiconductor fabrication (elemental, compound, and rare earth); Quantum Mechanical Tunneling Phenomena (Semi-conductor and Metals).

For Full Details, Write MELPAR, INC. F. J. Drummond, Professional Placement Manager, Melpar, 3002 Arlington Boulevard, Falls Church, Virginia.

All qualified applicants will be considered regardless of race, color, or national origin.

SOLID

Semi-conductor Research— Magnetics—Thin Films

Ph.D. Research Physicists: If you have reached a stage in your professional career that you find limiting, we will be happy to pursue the matter of new employment in our Physical Research Laboratories at Dayton, Ohio.

Recent developments and program changes require that only scientists capable of extending themselves into new areas of semi-conductor research be considered. Awareness of semi-conductor potential and epitaxial techniques is mandatory. In areas of Magnetic Research a background of studies involving the properties of magnetic materials and thin films is desirable. However, rather than establish arbitrary requirements that limit your reaction to this invitation, we prefer to leave all matters open.

Our primary business is furnishing the world with the best and most advanced data handling systems. This is achieved through long-range planning and realistic research. We would appreciate a brief letter describing the basic elements of your background, which you believe have prepared you for the next step in your scientific and personal development.

T. F. Wade, Technical Placement 118

THE NATIONAL CASH REGISTER COMPANY Dayton 9, Ohio Transactions of the Society of Rheology. According to the Society, the presentation of papers at the meeting is not restricted to members of the organization. Local arrangements for the meeting are in the hands of a committee headed by John D. Ferry, University of Wisconsin, Madison, Wisc.

A preliminary announcement has also been made of plans for a meeting still two years in the future—the Fourth International Congress of Rheology. The Congress will be held August 26-30, 1963, at Brown University, Providence, R. I. R. S. Marvin of the National Bureau of Standards and R. S. Rivlin of Brown have been appointed cochairmen of the Steering Committee. Prof. Rivlin has also been named to head the Local Arrangements Committee for the Congress, and all communications concerning the Congress should be addressed to him.

APS Division of Fluid Dynamics

V ARIOUS aspects of the physics of fluids, including hydrodynamics and surface waves, magneto-fluid dynamics, rarefied gas dynamics, shock-tube and shock-tunnel flows, turbulence and boundary layer phenomena, superfluidity, medical hydrodynamics, and astral fluid dynamics, are topics to be covered at the 1961 meeting of the American Physical Society's Division of Fluid Dynamics. The annual gathering will take place November 20–22 in Berkeley, Calif.

Short abstracts (under 200 words) of papers to be contributed should be sent in duplicate before October 9 to the chairman of the Program Committee, Wayland C. Griffith, Lockheed Missiles and Space Division, Palo Alto, Calif. Additional information on the Division and on the meeting can be obtained from the secretary-treasurer, Raymond J. Emrich, Department of Physics, Lehigh University, Bethlehem, Pa.

Crystal Lattice Defects

A^N International Conference on Crystal Lattice Defects is being organized by the Physical Society of Japan and is scheduled to take place in Kyoto from September 7 to 12, 1962. In order to maintain the aim of the conference, which is to obtain a clearer understanding of lattice defects, attendance will be limited to active workers in the field and to others who may be preparing to engage in such work.

The program of the 1962 conference will cover point defects in metals, semiconductors, and ionic crystals as well as extended defects closely related to point defects. Suggested items for discussion are electronic processes in imperfect crystals, properties of single and multiple point defects, radiation damage, association, dissociation, and diffusion of point defects. Purely phenomenological studies will not be included, nor will work that is ambiguous from the viewpoint of lattice defects.

Persons wishing to participate are invited to write to the Lattice Defects Conference Secretariat, c/o Prof. R. R. Hasiguti, Department of Metallurgy, University of Tokyo, Bunkyo-ku, Tokyo, Japan.